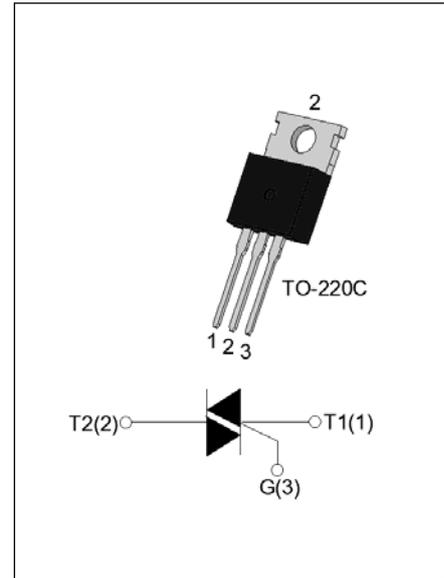


DESCRIPTION:

The JST08C-600B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT} / / /$	50/50/50/70	mA



ABSOLUTE MAXIMUM RATINGS

Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c = 108^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	100	$\text{A}/\mu\text{s}$
	-	50	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{PP}	1	kV



ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		ALL	MAX.	70	
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	ALL	MIN.	1	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	0.2	V
I_H		$I_T=200mA$	MAX.	50	100
dV/dt	$V_D=400V$ Gate Open $T_j=125$	MIN.	60	1200	$V/\mu s$
$(dV/dt)_c$	$(dI/dt)_c=3.5A/ms, T_j=125$	MIN.	12	12	$V/\mu s$
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$	TYP.	5	30	μs
t_{off}		TYP.	30		

STATIC CHARACTERISTICS

V_{TM}	$I_{TM}=11A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.81	V
R_D	Dynamic resistance	$T_j=125$	44	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.25	mA

THERMAL RESISTANCES

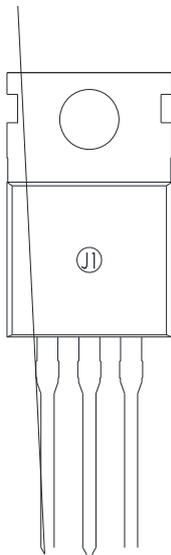
$R_{th(j-c)}$	junction to case (AC)	1.5	$/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$/W$



ORDERING INFORMATION

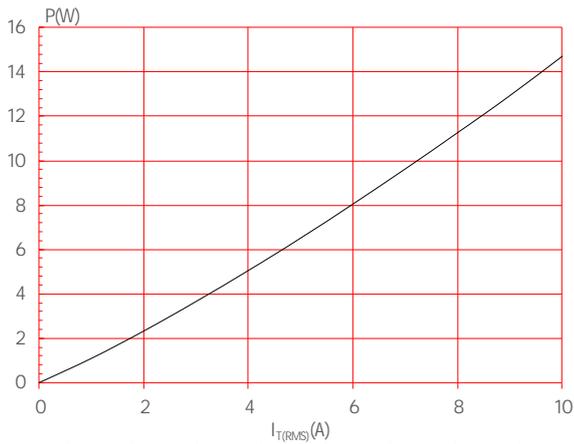
J	ST	08	C	-600	B
JieJie Microelectronics Co., Ltd	Triacs	$I_{T(RMS)}: 8A$	C: TO-220C	600: $V_{DRM} / V_{RRM} \quad 600V$	B: $I_{GT1-3} \quad 50mA \quad I_{GT4} \quad 70mA$

MARKING

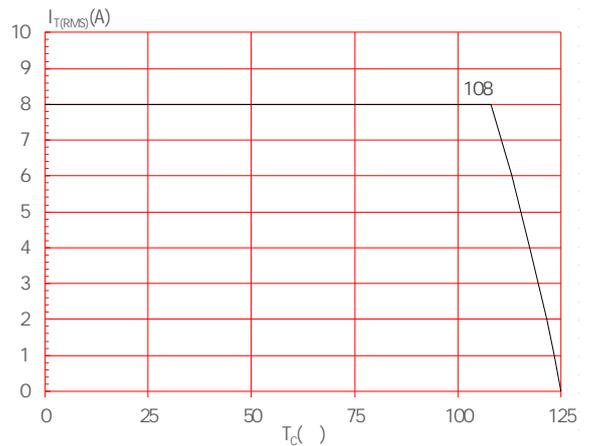




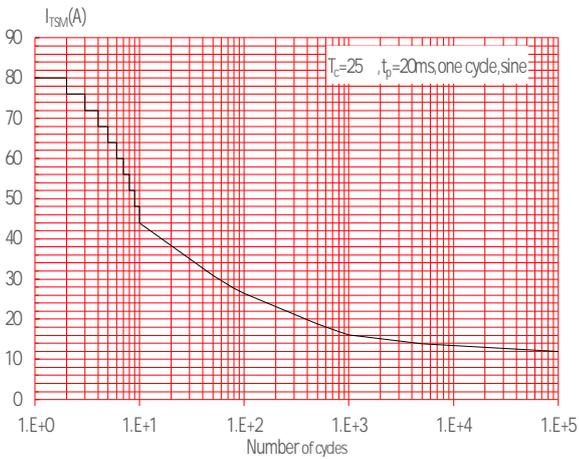
Maximum power dissipation versus RMS on-state current



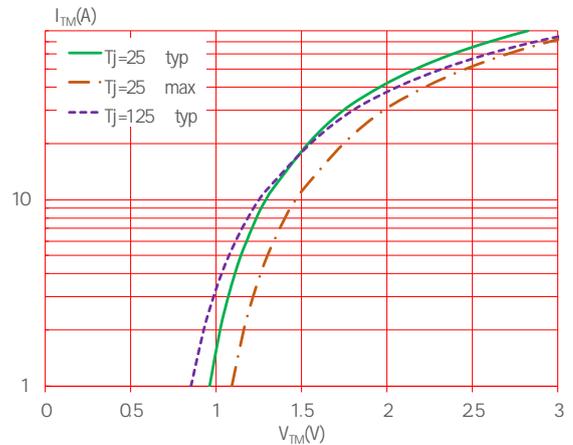
RMS on-state current versus case temperature



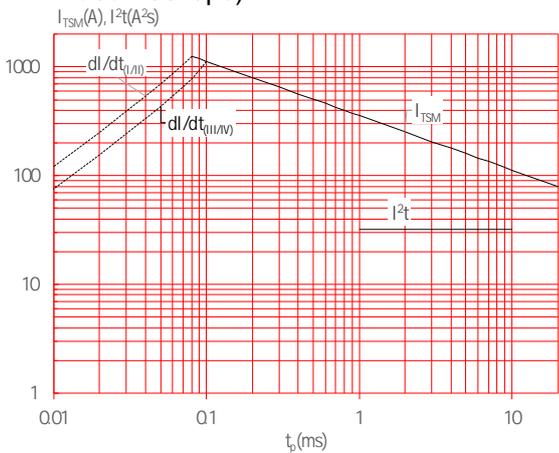
Surge peak on-state current versus number of cycles



On-state characteristics



Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 100\text{A}/\mu\text{s}$; $dI/dt < 50\text{A}/\mu\text{s}$)



Relative variations of gate trigger current, holding current and latching current versus junction temperature

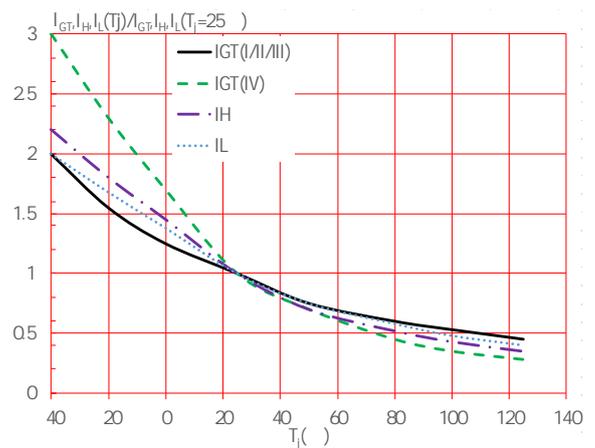
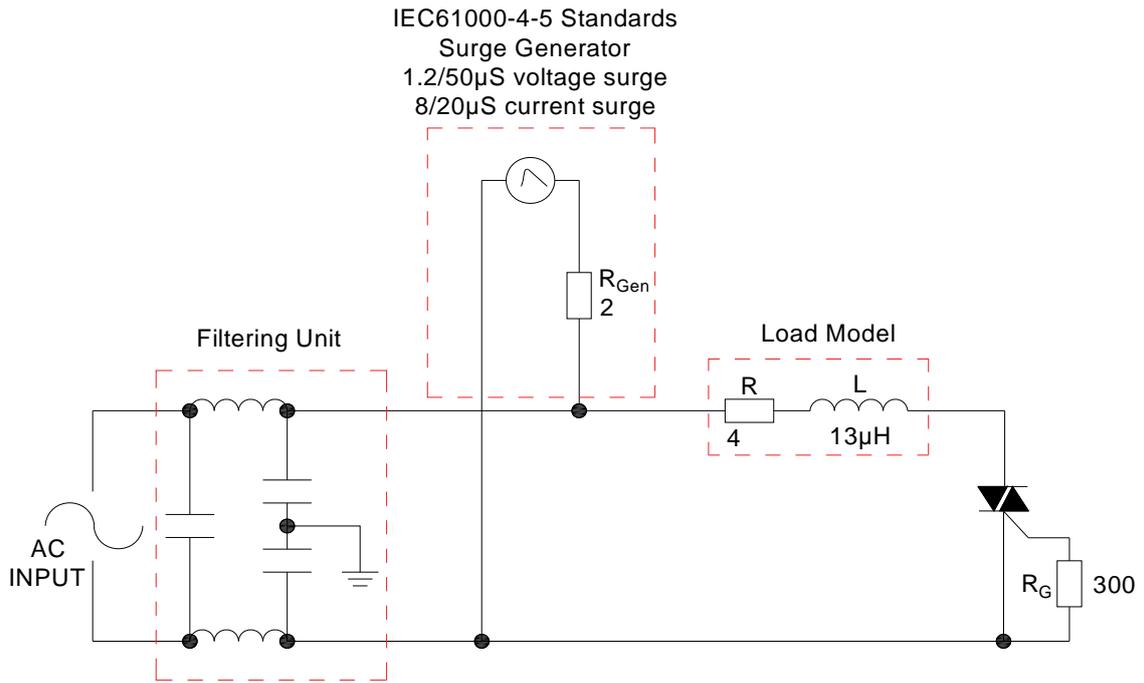


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie.

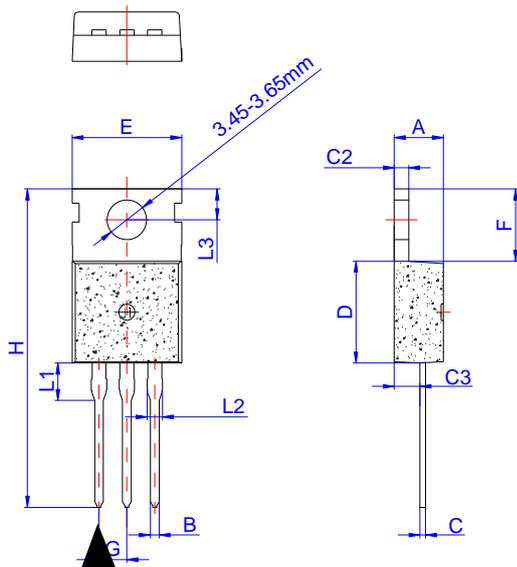


ORDERING INFORMATION

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

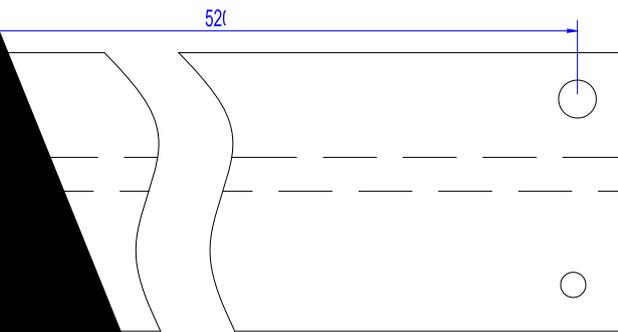


PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE





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